

**isc Silicon NPN Power Transistor**

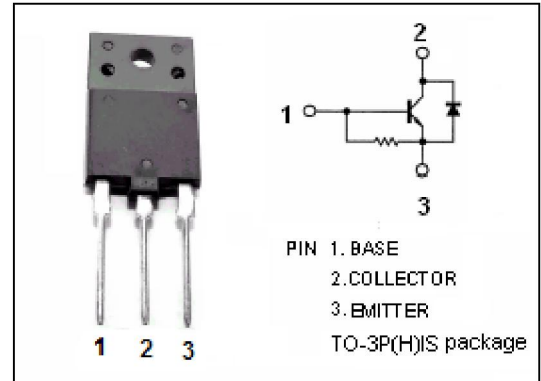
**BU2527DX**

**DESCRIPTION**

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

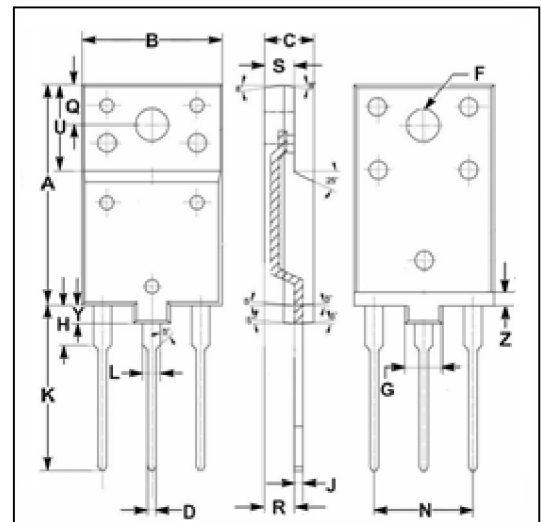
**APPLICATIONS**

- Designed for use in horizontal deflection circuits of high resolution monitors.



**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7.5	V
I <sub>C</sub>	Collector Current-Continuous	12	A
I <sub>CM</sub>	Collector Current-peak	30	A
I <sub>B</sub>	Base Current-Continuous	8	A
I <sub>BM</sub>	Base Current-peak	12	A
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C	45	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



DIM	mm	
	MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.8	K/W

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## BU2527DX

## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0, L=25\text{mH}$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=600\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			1.1	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=BV_{CES}; V_{BE}=0$ $V_{CE}=BV_{CES}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$		110		mA
$h_{FE-1}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		11		
$h_{FE-2}$	DC Current Gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	5	7	10	
$V_{ECF}$	C-E Diode Forward Voltage	$I_F=8\text{A}$			2.0	V
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{\text{test}}=1\text{MHz}$		145		pF

## Switching times

$t_{stg}$	Storage Time	$I_C=6\text{A}, I_{B(\text{end})}=0.55\text{A}; L_B=0.6\mu\text{H}$ $-V_{BB}=4\text{V}; -I_{BM}=3.6\text{A}$			2.0	$\mu\text{s}$
$t_f$	Fall Time				0.2	$\mu\text{s}$